

## REMARKS/ARGUMENTS

Claims 1-7 and 11-21 are generic claims.

Regarding claim 9, it should be noted that the description of Fig. 4 states that both the GaN layer (first nitride compound semiconductor material) as the AlGaIn layer (second nitride compound semiconductor material) are n-doped (see par. [0063] of the present specification). Thus, claim 9 is readable on the elected species.

Applicants reserve the right to pursue the non-elected claims in a divisional application prior to issuance of a patent on the instant application.

Any additional fees or charges required at this time in connection with the application may be charged to our Patent and Trademark Office Deposit Account No. 03-2412.

Respectfully submitted,  
COHEN PONTANI LIEBERMAN & PAVANE LLP

By /Thomas Langer/  
Thomas Langer  
Reg. No. 27,264  
551 Fifth Avenue, Suite 1210  
New York, New York 10176  
(212) 687-2770

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